

M74HCT32

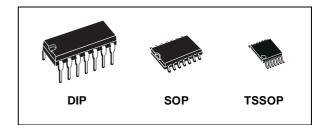
QUAD 2-INPUT OR GATE

- HIGH SPEED: t_{PD} = 13ns (TYP.) at V_{CC} = 4.5V
- LOW POWER DISSIPATION: $I_{CC} = 1\mu A(MAX.)$ at $T_A=25^{\circ}C$
- COMPATIBLE WITH TTL OUTPUTS : V_{IH} = 2V (MIN.) V_{IL} = 0.8V (MAX)
- BALANCED PROPAGATION DELAYS: t_{PLH} ≅ t_{PHL}
- SYMMETRICAL OUTPUT IMPEDANCE: |I_{OH}| = I_{OL} = 4mA (MIN)
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 32

DESCRIPTION

The M74HCT32 is an high speed CMOS QUAD 2-INPUT OR GATE fabricated with silicon gate C^2MOS technology.

The internal circuit is composed of 2 stages including buffer output, which enables high noise immunity and stable output.



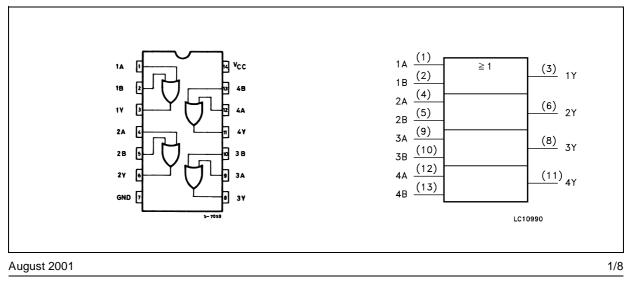
ORDER CODES

PACKAGE	TUBE	T & R
DIP	M74HCT32B1R	
SOP	M74HCT32M1R	M74HCT32RM13TR
TSSOP		M74HCT32TTR

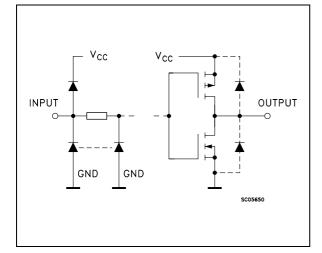
The M74HCT32 is designed to directly interface HSC^2MOS systems with TTL and NMOS components.

All inputs are equipped with protection circuits against static discharge and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 4, 9, 12	1A to 4A	Data Inputs
2, 5, 10, 13	1B to 4B	Data Inputs
3, 6, 8, 11	1Y to 4Y	Data Outputs
7	GND	Ground (0V)
14	V _{CC}	Positive Supply Voltage

TRUTH TABLE

A	В	Y
L	L	L
L	Н	Н
Н	L	Н
Н	Н	Н

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ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7	V
VI	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
Vo	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
۱ ₀	DC Output Current	± 25	mA
$I_{\rm CC}$ or $I_{\rm GND}$	DC V _{CC} or Ground Current	± 50	mA
PD	Power Dissipation	500(*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
ΤL	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is (*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	4.5 to 5.5	V
VI	Input Voltage	0 to V _{CC}	V
Vo	Output Voltage	0 to V _{CC}	V
T _{op}	Operating Temperature	-55 to 125	°C
t _r , t _f	Input Rise and Fall Time ($V_{CC} = 4.5$ to 5.5V)	0 to 500	ns

DC SPECIFICATIONS

		1	Test Condition				Value				
Symbol	Symbol Parameter		V _{cc}		T _A = 25°C			85°C	-55 to 125°C		Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V _{IH}	High Level Input Voltage	4.5 to 5.5		2.0			2.0		2.0		V
V _{IL}	Low Level Input Voltage	4.5 to 5.5				0.8		0.8		0.8	V
V _{OH}	High Level Output	4.5	I _O =-20 μA	4.4	4.5		4.4		4.4		V
	Voltage	4.5	I _O =-4.0 mA	4.18	4.31		4.13		4.10		v
V _{OL}	Low Level Output	4.5	I _O =20 μA		0.0	0.1		0.1		0.1	V
	Voltage	4.5	I _O =4.0 mA		0.17	0.26		0.33		0.40	v
I	Input Leakage Current	5.5	$V_{I} = V_{CC} \text{ or } GND$			± 0.1		± 1		± 1	μΑ
Icc	Quiescent Supply Current	5.5	$V_{I} = V_{CC} \text{ or } GND$			1		10		20	μΑ
ΔI _{CC}	Additional Worst Case Supply Current	5.5	Per Input pin $V_I = 0.5V$ or $V_I = 2.4V$ Other Inputs at V_{CC} or GND $I_O = 0$			2.0		2.9		3.0	mA

AC ELECTRICAL CHARACTERISTICS (CL = 50 pF, Input $t_r = t_f = 6ns$)

		٦	Test Condition	Condition Value								
Symbol	Parameter	V _{CC} (V)	v _{cc}		Т	_A = 25°	С	-40 to	85°C	-55 to	125°C	Unit
				Min.	Тур.	Max.	Min.	Max.	Min.	Max.		
t _{TLH} t _{THL}	Output Transition Time	4.5			8	15		19		23	ns	
t _{PLH} t _{PHL}	Propagation Delay Time	4.5			13	21		26		32	ns	

CAPACITIVE CHARACTERISTICS

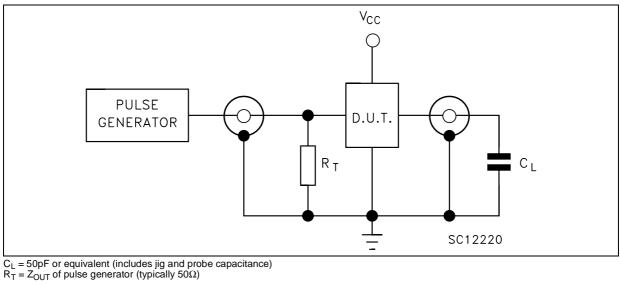
		٦	Test Condition		Value							
Symbol	Parameter	V _{cc}	V _{CC}	v _{cc}	T _A = 25°C			-40 to 85°C		-55 to 125°C		Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.		
C _{IN}	Input Capacitance				5	10		10		10	pF	
C _{PD}	Power Dissipation Capacitance (note 1)				39						pF	

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/4$ (per gate)

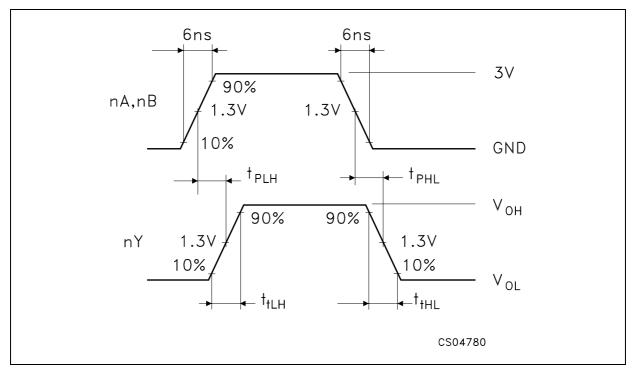


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TEST CIRCUIT



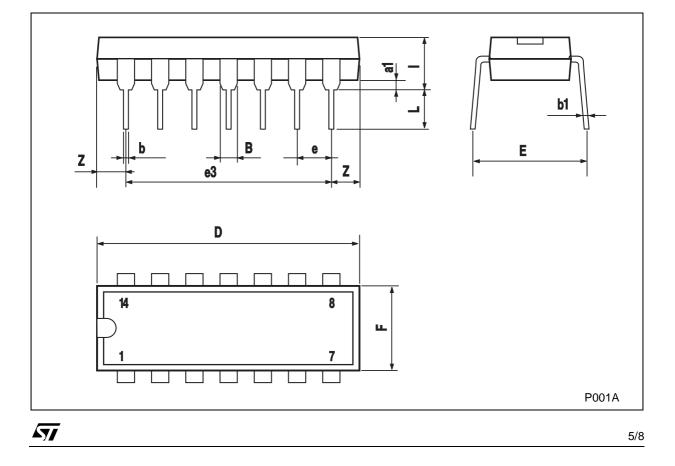
WAVEFORM : PROPAGATION DELAY TIMES (f=1MHz; 50% duty cycle)



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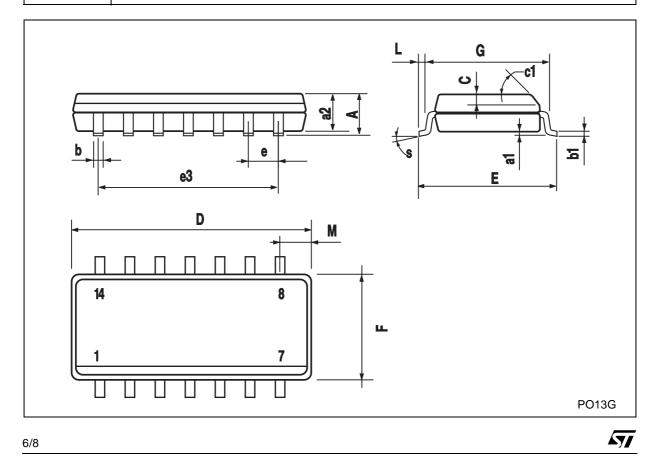
DIM.		mm.		inch					
DIM.	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.			
a1	0.51			0.020					
В	1.39		1.65	0.055		0.065			
b		0.5			0.020				
b1		0.25			0.010				
D			20			0.787			
E		8.5			0.335				
е		2.54			0.100				
e3		15.24			0.600				
F			7.1			0.280			
Ι			5.1			0.201			
L		3.3			0.130				





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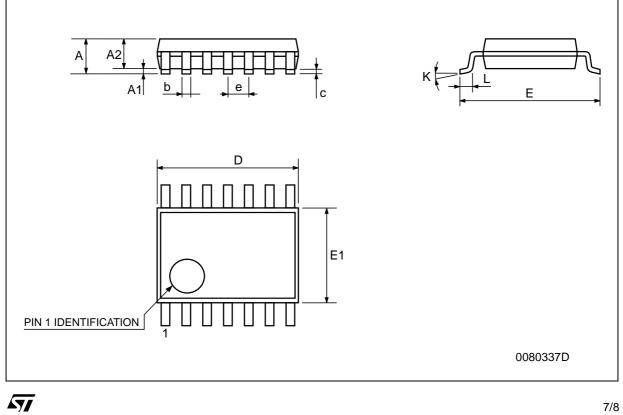
	SO-14 MECHANICAL DATA											
DIM		mm.			inch							
DIM.	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.						
А			1.75			0.068						
a1	0.1		0.2	0.003		0.007						
a2			1.65			0.064						
b	0.35		0.46	0.013		0.018						
b1	0.19		0.25	0.007		0.010						
С		0.5			0.019							
c1			45°	(typ.)		•						
D	8.55		8.75	0.336		0.344						
Е	5.8		6.2	0.228		0.244						
е		1.27			0.050							
e3		7.62			0.300							
F	3.8		4.0	0.149		0.157						
G	4.6		5.3	0.181		0.208						
L	0.5		1.27	0.019		0.050						
М			0.68			0.026						
S		•	8° (r	max.)	•	•						



MECHANICAL <u>а т а</u> . .

DIM.		mm.		inch				
Dim.	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.		
А			1.2			0.047		
A1	0.05		0.15	0.002	0.004	0.006		
A2	0.8	1	1.05	0.031	0.039	0.041		
b	0.19		0.30	0.007		0.012		
С	0.09		0.20	0.004		0.0089		
D	4.9	5	5.1	0.193	0.197	0.201		
Е	6.2	6.4	6.6	0.244	0.252	0.260		
E1	4.3	4.4	4.48	0.169	0.173	0.176		
е		0.65 BSC			0.0256 BSC			
К	0°		8°	0°		8°		
L	0.45	0.60	0.75	0.018	0.024	0.030		





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